



STB160N75F3 STP160N75F3 - STW160N75F3

N-channel 75V - 3.5mΩ - 120A - TO-220 - TO-247 - D²PAK
STripFET™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} (max.)	I _D
STB160N75F3	75V	3.7 mΩ	120 A ⁽¹⁾
STP160N75F3	75V	4 mΩ	120 A ⁽¹⁾
STW160N75F3	75V	4 mΩ	120 A ⁽¹⁾

1. Current limited by package

- Ultra low on-resistance
- 100% Avalanche tested

Application

- Switching applications

Description

This N-channel enhancement mode Power MOSFET is the latest refinement of ST's STripFET™ process. The resulting transistor shows extremely high packing density for low on resistance, rugged avalanche characteristics and low gate charge.

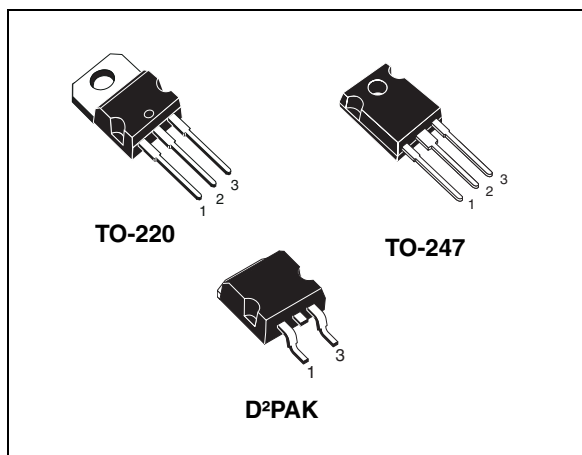


Figure 1. Internal schematic diagram

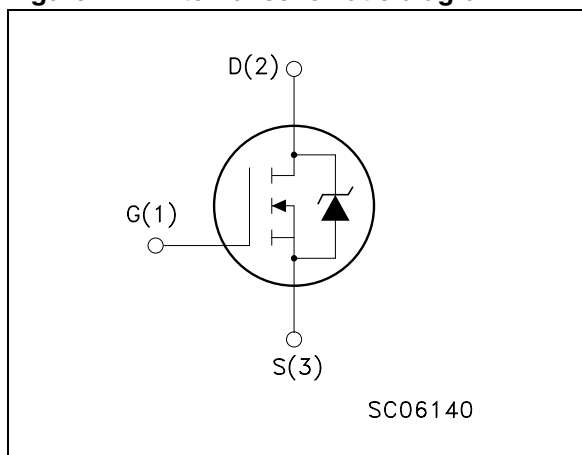


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB160N75F3	160N75F3	D ² PAK	Tape & reel
STP160N75F3	160N75F3	TO-220	Tube
STW160N75F3	160N75F3	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	75	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	330	W
	Derating factor	2.2	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	20	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	600	mJ
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. Current limited by package
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 120\text{A}$, $di/dt \leq 1100\text{ A}/\mu\text{s}$, $V_{DD} \leq 60\text{V}$, $T_J \leq T_{JMAX}$
4. Starting $T_J = 25^\circ\text{C}$, $I_D = 60\text{A}$, $V_{DD} = 25\text{V}$

Table 3. Thermal resistance

Symbol	Parameter	Value			Unit
		TO-220	TO-247	D ² PAK	
$R_{thj-case}$	Thermal resistance junction-case max	0.45			$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	50	--	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	--	--	50	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300			$^\circ\text{C}$

1. When mounted on 1 inch² FR4 2 oz Cu

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions		Min.	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0$		75			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating}$, @ 125°C				10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$				± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$		2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 60\text{A}$	TO-220 TO-247 D²PAK		3.5 3.2	4 3.7	$\text{m}\Omega$ $\text{m}\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		6750		pF
C_{oss}	Output capacitance			1080		pF
C_{rss}	Reverse transfer capacitance			40		pF
Q_g	Total gate charge	$V_{DD} = 37.5\text{V}$, $I_D = 120\text{A}$		85		nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{V}$		27		nC
Q_{gd}	Gate-drain charge	(see Figure 16)		26		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=37.5\text{ V}$, $I_D=60\text{ A}$, $R_G=4.7\Omega$, $V_{GS}=10\text{ V}$, (see Figure 18)		22		ns
t_r	Rise time			65		ns
$t_{d(off)}$	Turn-off delay time			100		ns
t_f	Fall time			15		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=120\text{ A}$, $V_{GS}=0$			1.5	V
t_{rr}	Reverse recovery time	$I_{SD}=120\text{ A}$, $V_{DD}=20\text{ V}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_j=25^\circ\text{C}$ (see Figure 17)		70		ns
Q_{rr}	Reverse recovery charge			150		nC
I_{RRM}	Reverse recovery current			4.2		A

1. Pulse with limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 / TO-247

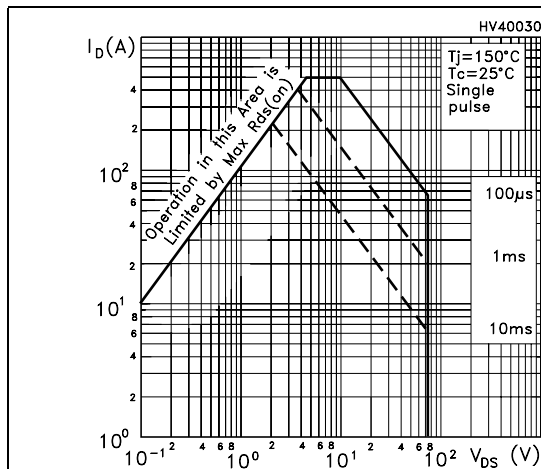


Figure 3. Thermal impedance for TO-220 / TO-247

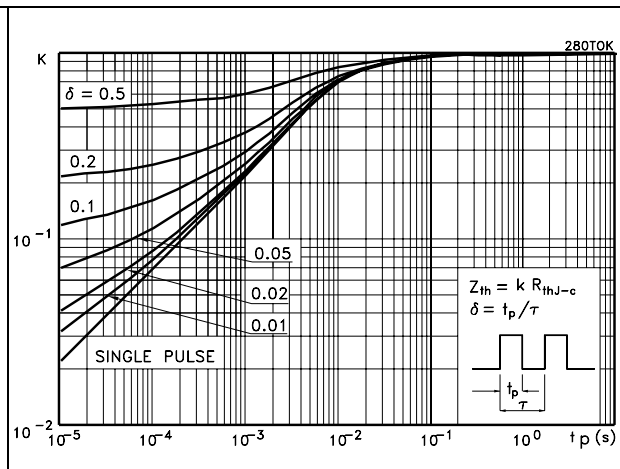


Figure 4. Safe operating area for D²PAK

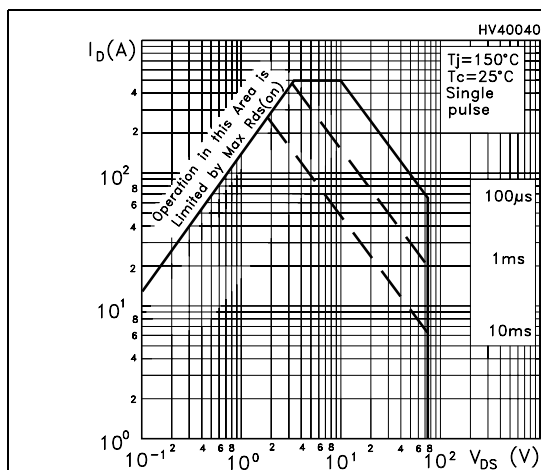


Figure 5. Thermal impedance for D²PAK

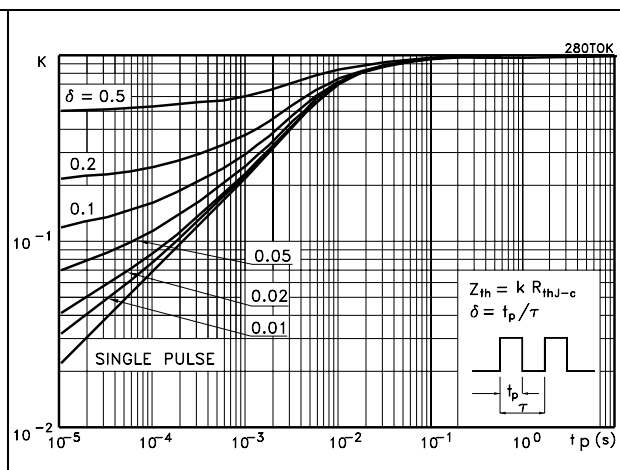


Figure 6. Output characteristics

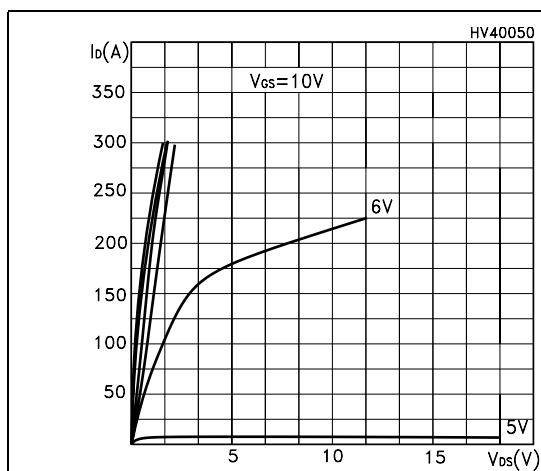


Figure 7. Transfer characteristics

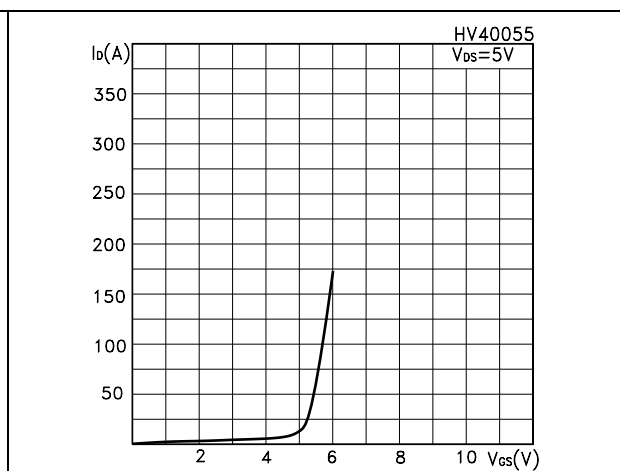


Figure 8. Normalized BV_{DSS} vs temperature Figure 9. Static drain-source on resistance

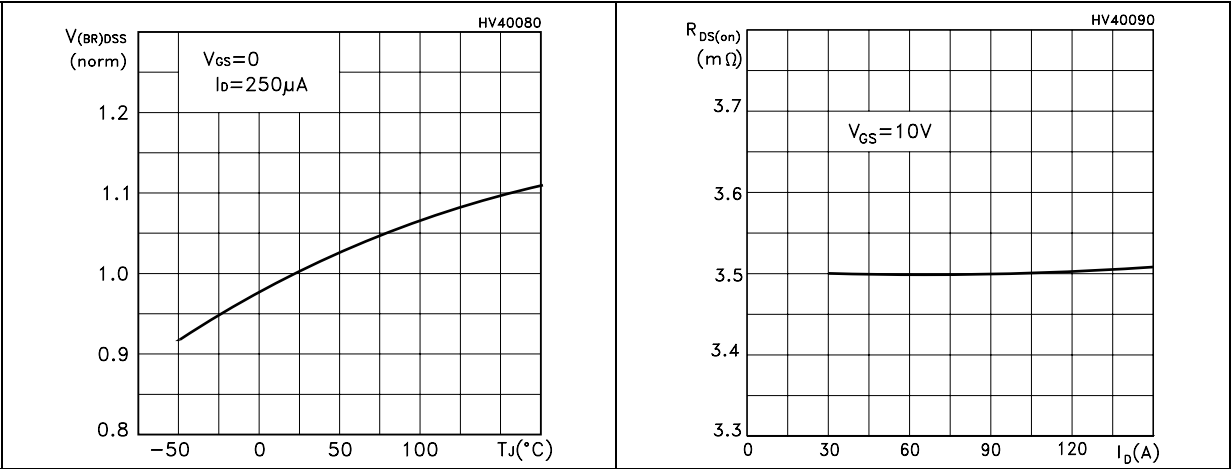


Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations

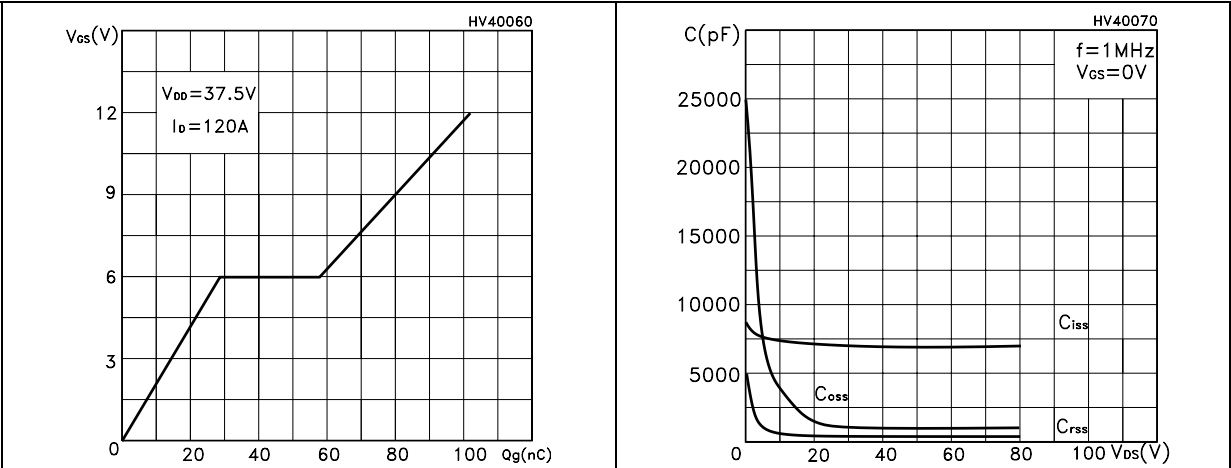


Figure 12. Normalized gate threshold voltage vs temperature Figure 13. Normalized on resistance vs temperature

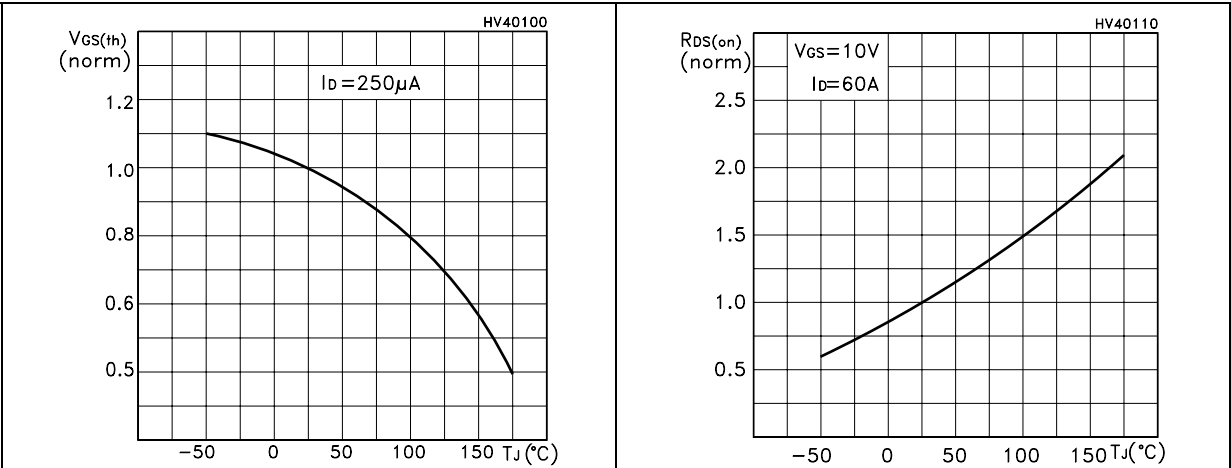
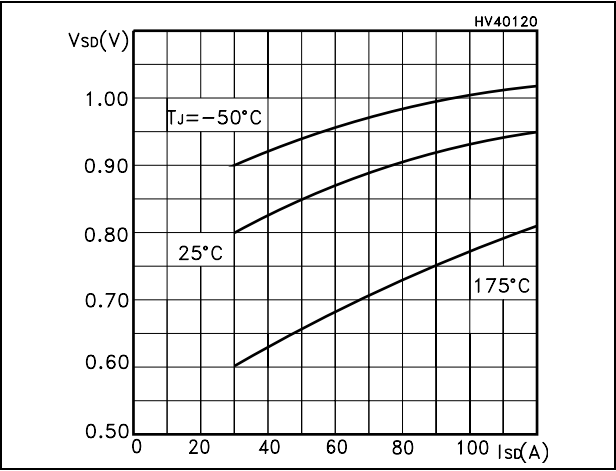


Figure 14. Source-drain diode forward characteristics



3 Test circuit

Figure 15. Switching times test circuit for resistive load

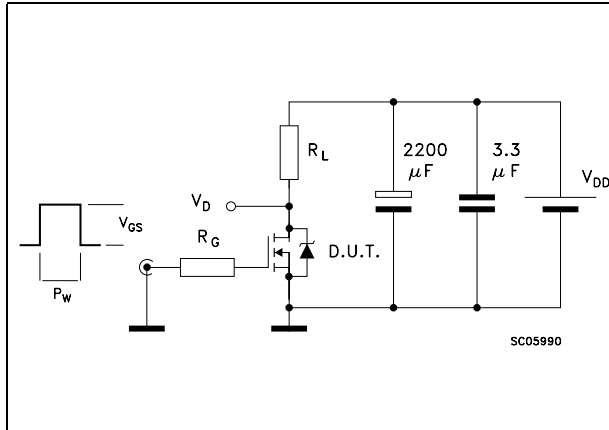


Figure 16. Gate charge test circuit

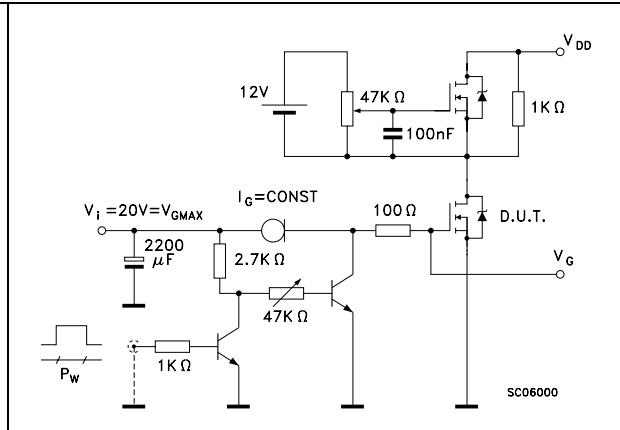


Figure 17. Test circuit for inductive load switching and diode recovery times

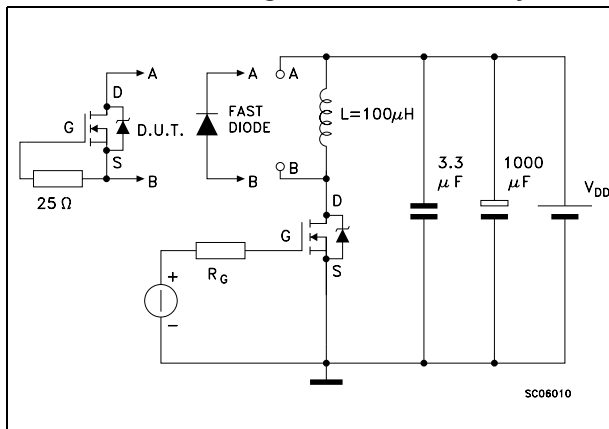


Figure 18. Unclamped inductive load test circuit

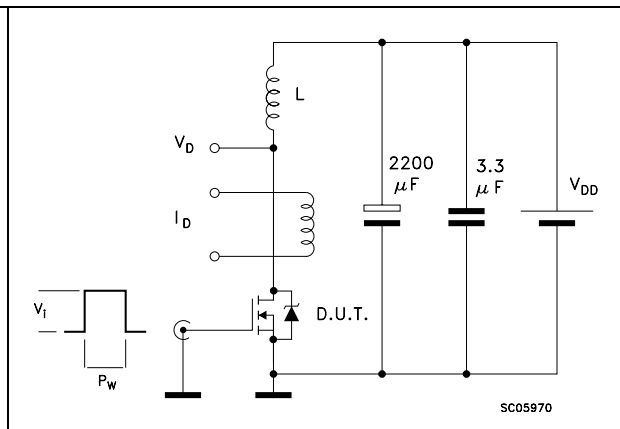


Figure 19. Unclamped inductive waveform

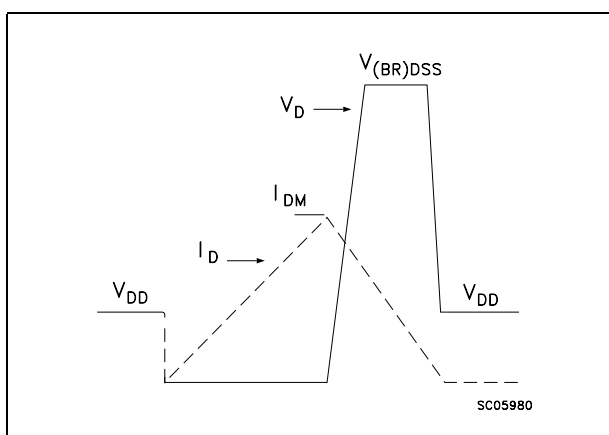
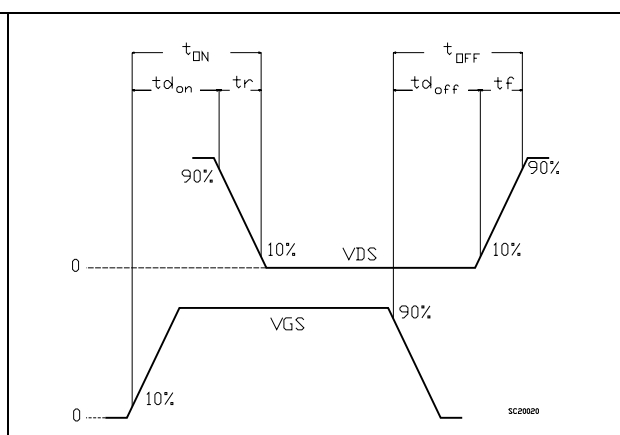


Figure 20. Switching time waveform

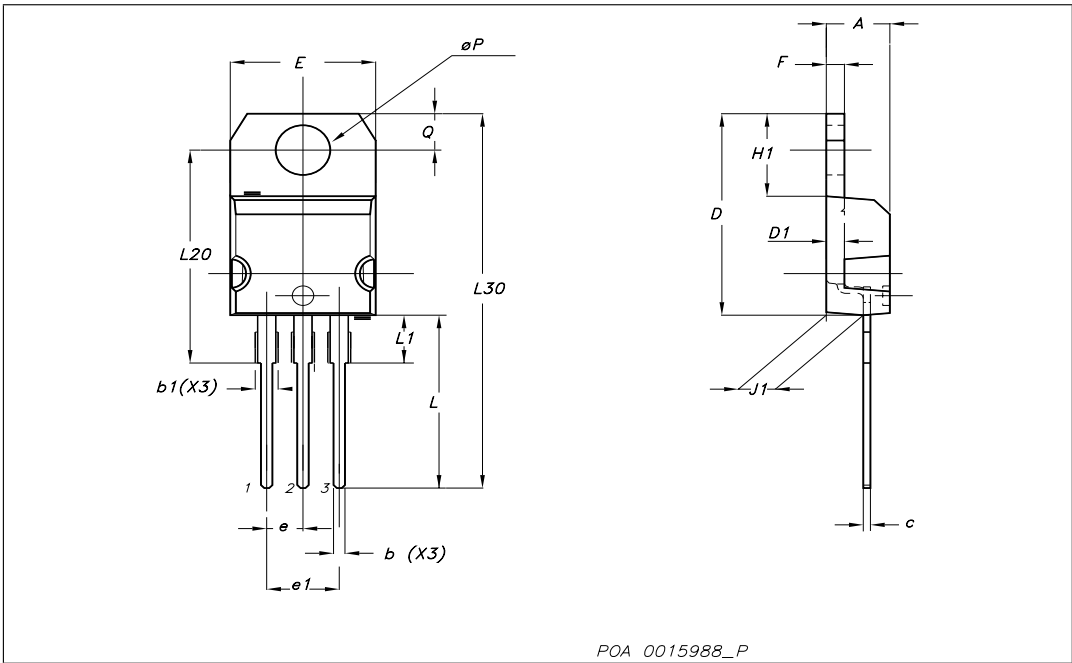


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

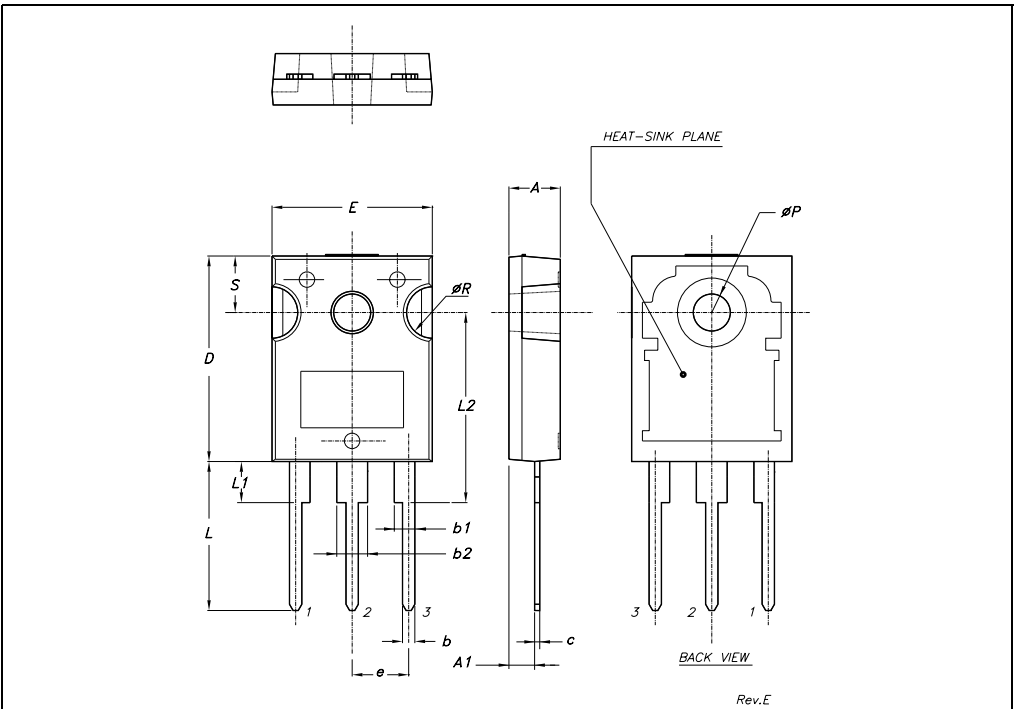
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



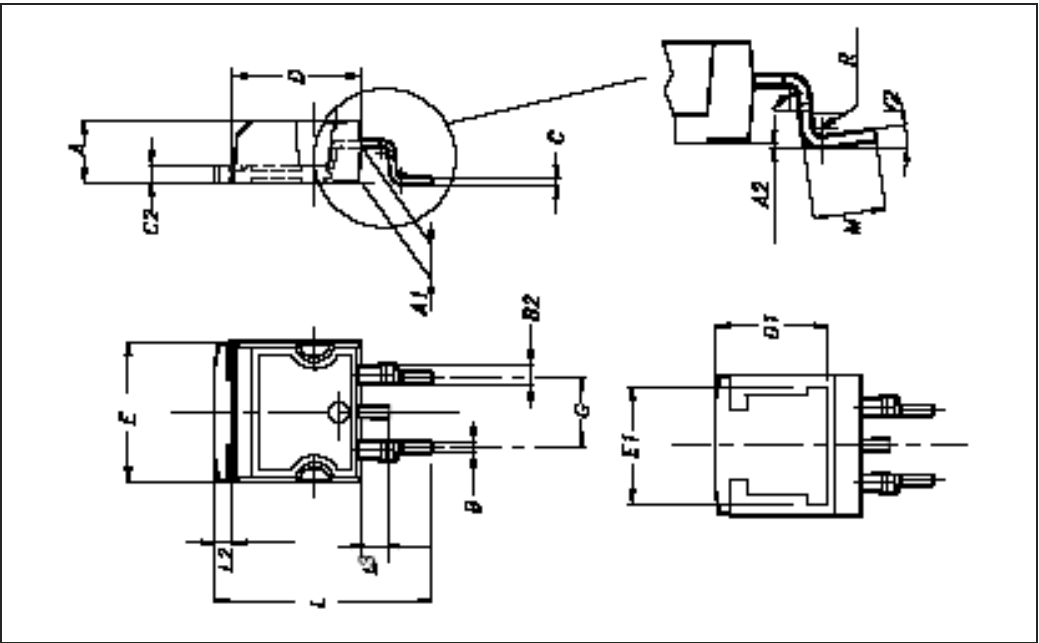
TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



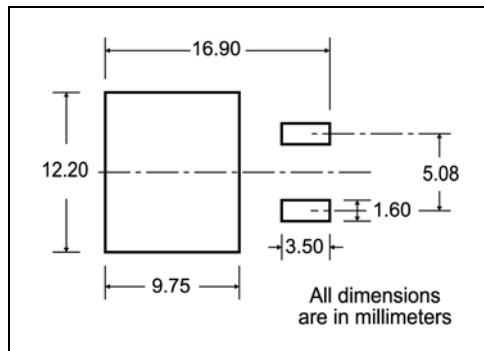
D²PAK mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.50		0.55
L3	1.4		1.75	0.055		0.68
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

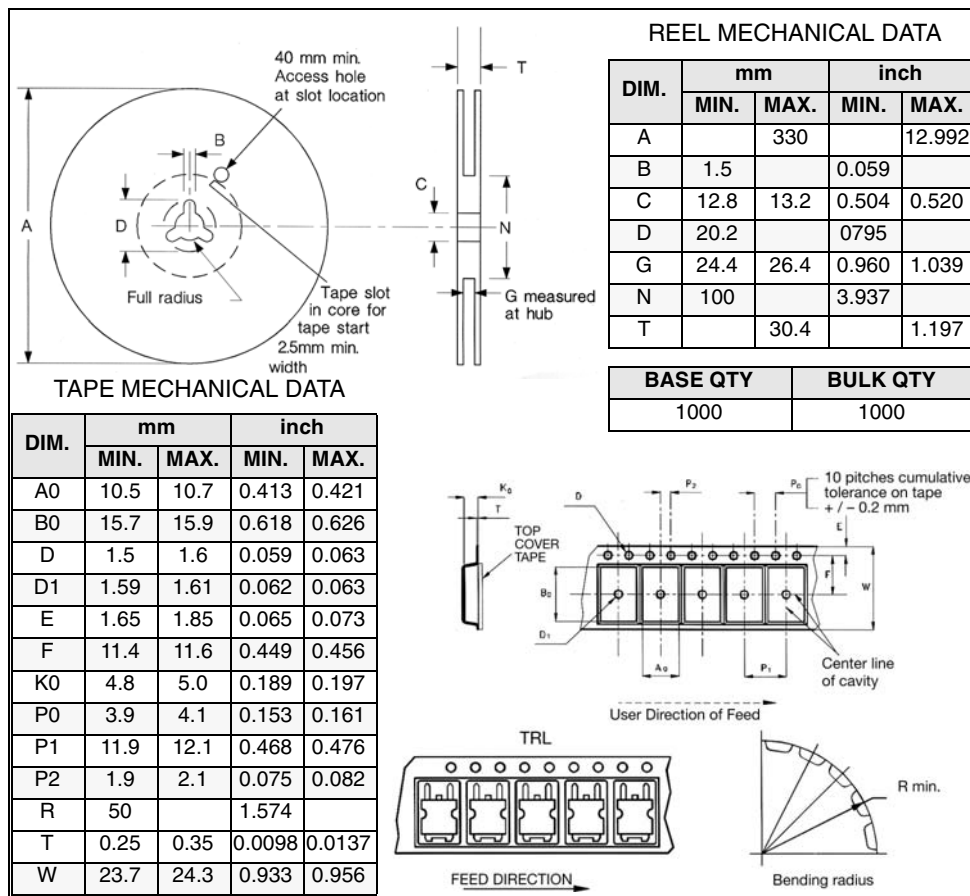


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
07-Feb-2007	1	First release
02-Oct-2007	2	New section has been added: <i>Electrical characteristics (curves)</i>

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